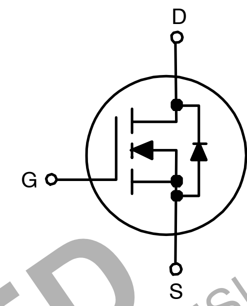
MOSFET – Power, Single, N-Channel, TOLL

60 V, 0.75 mΩ, 470 A

NTBLS0D7N06C

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
60 V	0.75 mΩ @ 10 V	470 A
	1.2 mΩ @ 6 V	



H−PSOF8L
CASE 100CU

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- Lowers Switching Noise/EMI
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	60	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	T_C = 25°C	I_D	470	A
Power Dissipation $R_{\theta JC}$ (Note 2)		T_C = 25°C	P_D	314	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	I_D	54	A
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		T_A = 25°C	P_D	4.2	W
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	900	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	260	A
Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 40 A)			E_{AS}	800	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case − Steady State (Note 2)	$R_{\theta JC}$	0.48	°C/W
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	36	

1. Surface−mounted on FR4 board using a 1 in^2 pad size, 2 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

ORDERING INFORMATION

Device	Package	Shipping†
NTBLS0D7N06C	H−PSOF8L (Pb−Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Table 1. ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Units
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 250 μA, V_{GS} = 0 V		60			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 661 μA, ref to 25°C			26.5		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V	T_J = 25°C			10	μA
			T_J = 125°C			100	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 661 μA		2.0	2.8	4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(th)}/T_J$	I_D = 661 μA, ref to 25°C			9.8		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 80 A			0.56	0.75	mΩ
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 6 V, I_D = 66 A			0.85	1.20	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 10 V, I_D = 80 A			310		S
Gate−Resistance	R_G	T_A = 25°C			0.6		Ω
CHARGES & CAPACITANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 30 V, f = 10 kHz			13730		pF
Output Capacitance	C_{oss}				6912		pF
Reverse Transfer Capacitance	C_{rss}				92		pF
Total Gate Charge	$Q_{G(tot)}$	V_{GS} = 10 V, V_{DS} = 30 V, I_D = 80 A			170		nC
Threshold Gate Charge	$Q_{G(th)}$				39		nC
Gate−to−Source Charge	Q_{gs}				62		nC
Gate−to−Drain Charge	Q_{gd}				16		nC
Total Gate Charge	$Q_{G(tot)}$	V_{GS} = 6 V, V_{DS} = 30 V, I_D = 80 A			102		nC
SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 3)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 30 V, I_D = 80 A, R_G = 6 Ω			37		ns
Rise Time	t_r				57		ns
Turn−Off Delay Time	$t_{d(off)}$				146		ns
Fall Time	t_f				105		ns
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	I_S = 80 A, V_{GS} = 0 V	T_J = 25°C		0.79	1.2	V
		I_S = 80 A, V_{GS} = 0 V	T_J = 125°C		0.66		V
Reverse Recovery Time	t_{rr}	V_{GS} = 0 V, dI_S/d_t = 100 A/μs, I_S = 66 A			132		ns
Charge Time	t_a				64		ns
Discharge Time	t_b				68		ns
Reverse Recovery Charge	Q_{rr}				386		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

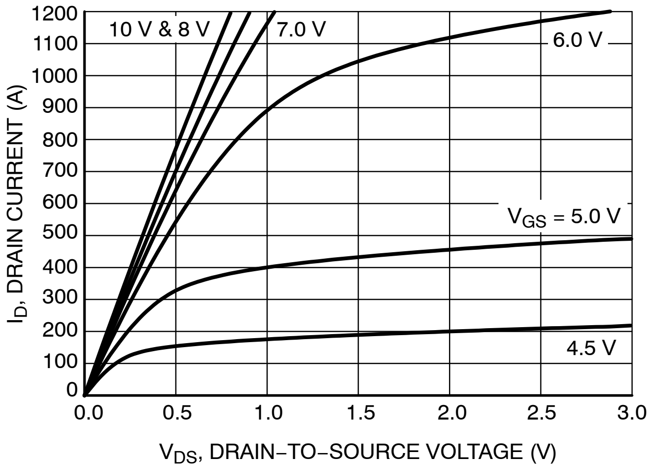


Figure 1. On−Region Characteristics

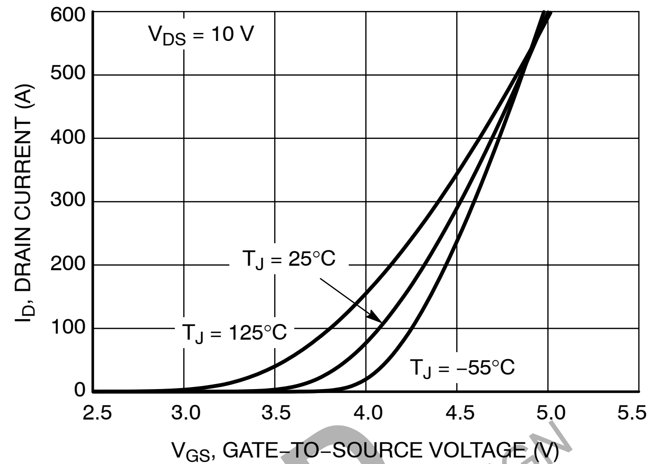


Figure 2. Transfer Characteristics

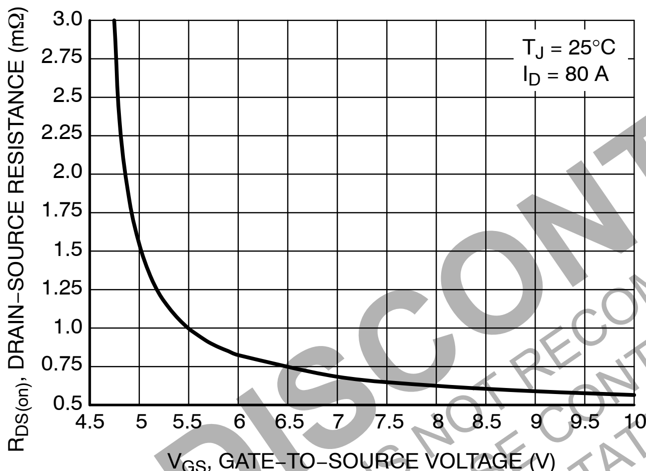


Figure 3. On−Resistance vs. V_{GS}

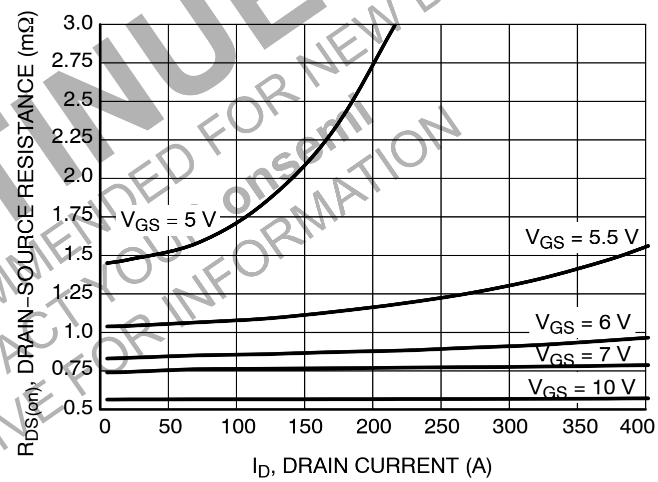


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

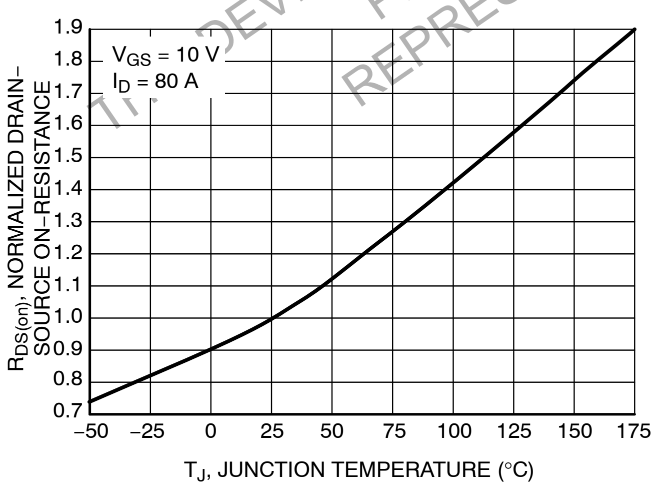


Figure 5. On−Resistance Variation with Temperature

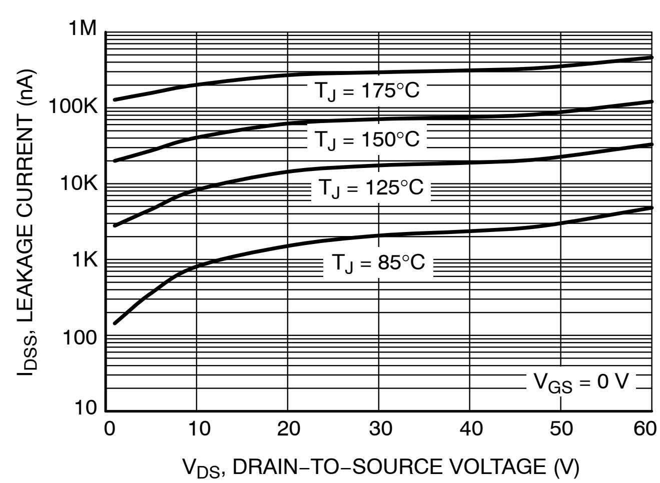


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

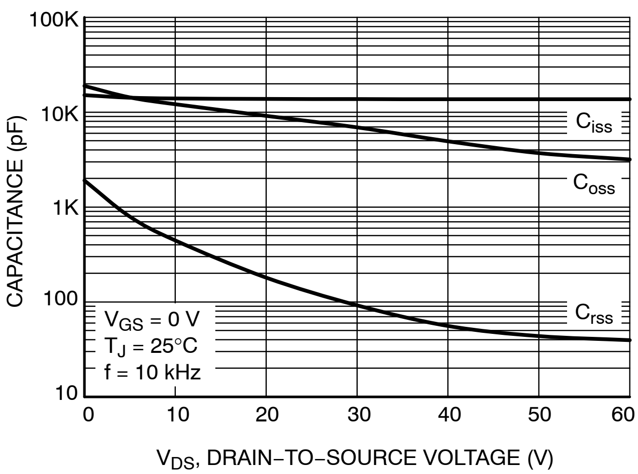


Figure 7. Capacitance Variation

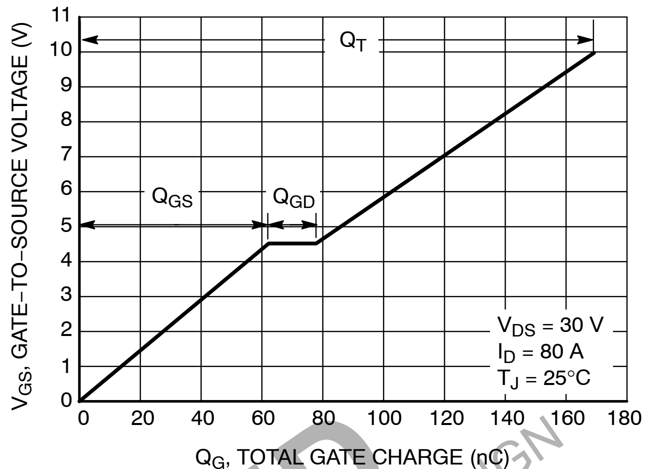


Figure 8. Gate−to−Source Voltage vs. Total Gate Charge

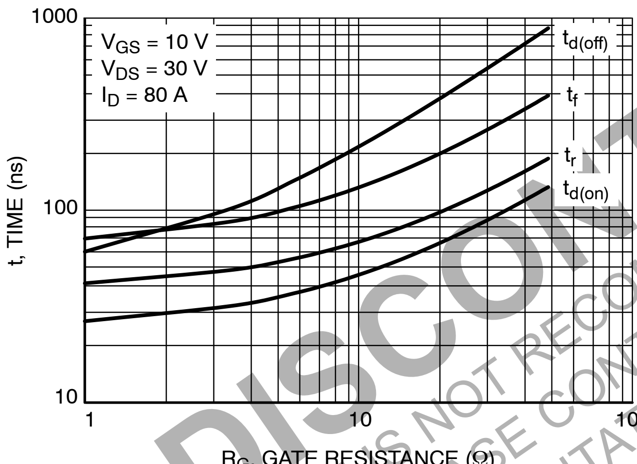


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

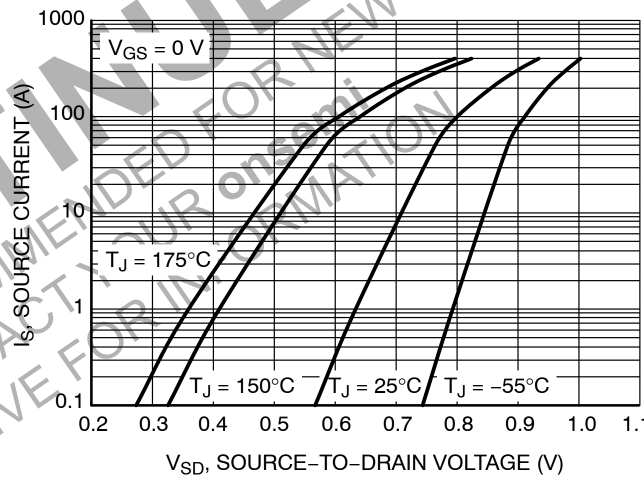


Figure 10. Diode Forward Voltage vs. Current

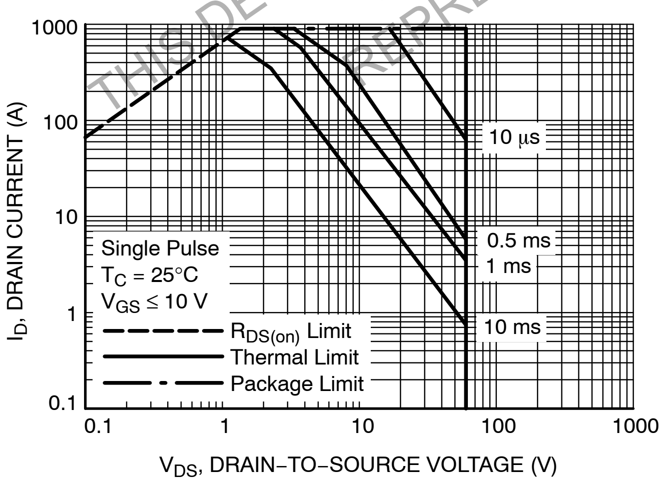


Figure 11. Maximum Rated Forward Biased Safe Operating Area

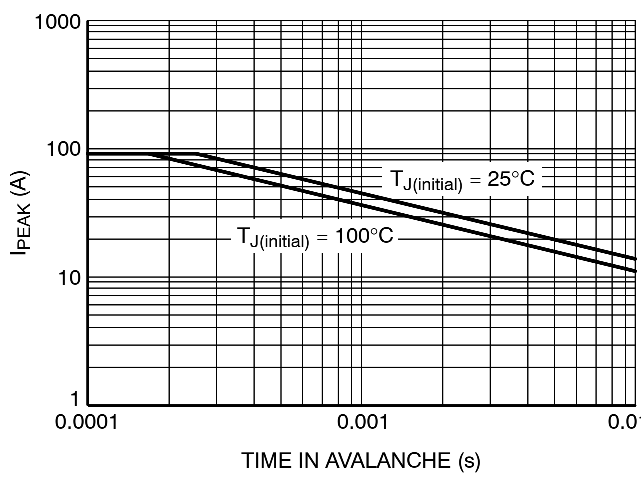


Figure 12. I_{PEAK} vs. Time in Avalanche

TYPICAL CHARACTERISTICS

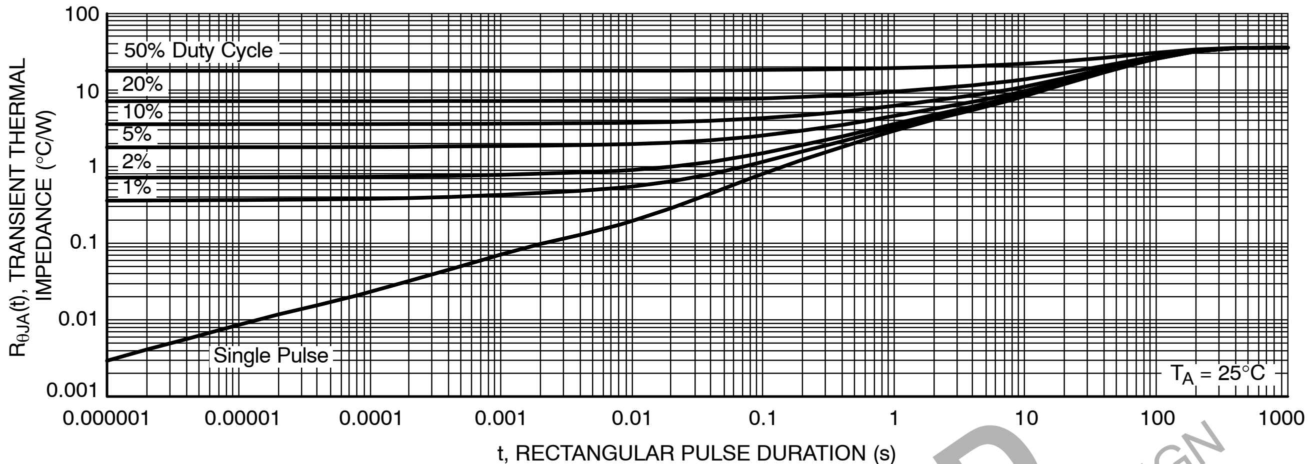


Figure 13. Thermal Response (Junction−to−Ambient)

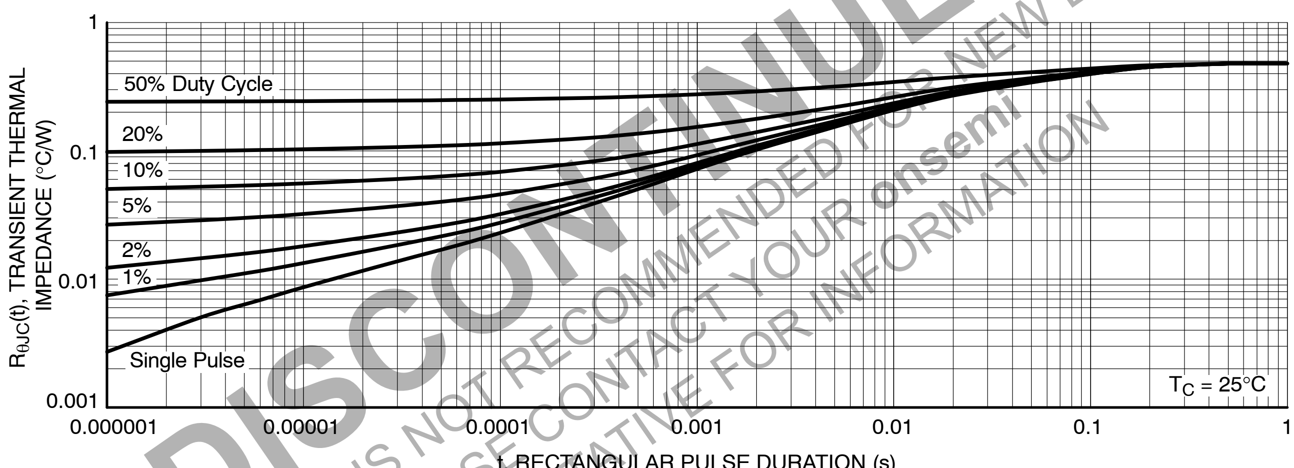
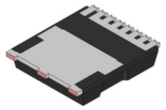
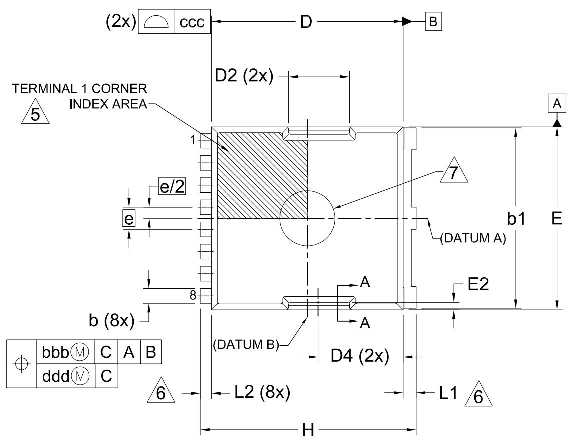


Figure 14. Thermal Response

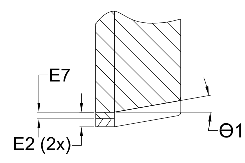


H−PSOF8L 11.68x9.80x2.30, 1.20P
CASE 100CU
ISSUE F

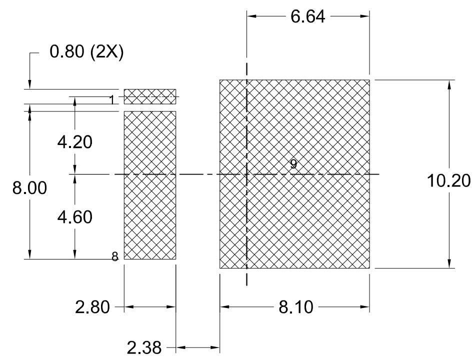
DATE 30 JUL 2024



TOP VIEW

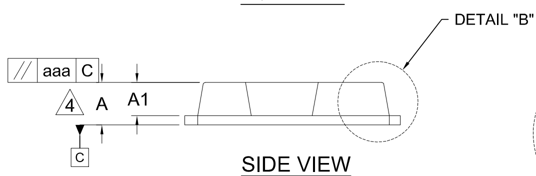


SECTION "A-A"
SCALE: 2X

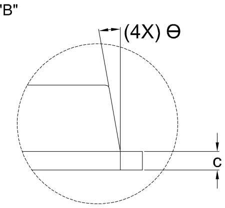


LAND PATTERN
RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

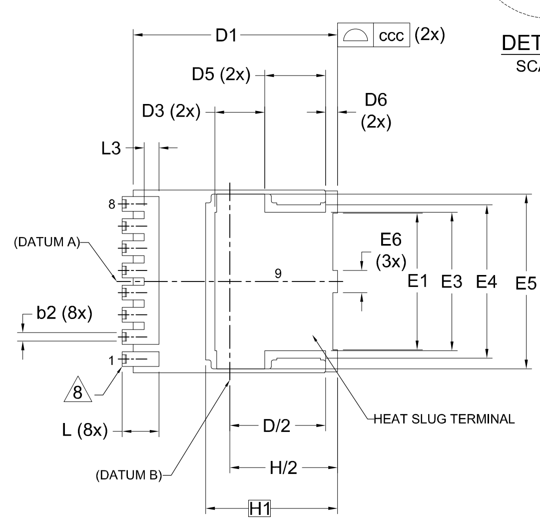


SIDE VIEW



DETAIL "B"
SCALE: 2X

NOTES:
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
3. "e" REPRESENTS THE TERMINAL PITCH.
4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g.,EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
6. DIMENSIONS b1,L1,L2 APPLY TO PLATED TERMINALS.
7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.



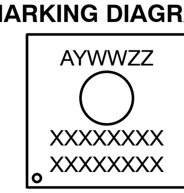
BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.35	0.45	0.55
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D/2	5.09	5.19	5.29
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	2.60	2.70	2.80
D4	4.45	4.55	4.65
D5	3.20	3.30	3.40
D6	0.55	0.65	0.75
E	9.80	9.90	10.00
E1	7.30	7.40	7.50
E2	0.30	0.40	0.50
E3	7.40	7.50	7.60
E4	8.20	8.30	8.40

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E5	9.36	9.46	9.56
E6	1.10	1.20	1.30
E7	0.15	0.18	0.21
e	1.20 BSC		
e/2	0.60 BSC		
H	11.58	11.68	11.78
H/2	5.74	5.84	5.94
H1	7.15 BSC		
L	1.90	2.00	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.70	0.80	0.90
Θ	10° REF		
Θ1	10° REF		
aaa	0.20		
bbb	0.25		
ccc	0.20		
ddd	0.20		
eee	0.10		

GENERIC MARKING DIAGRAM*

A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code
XXXX = Specific Device Code



*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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